

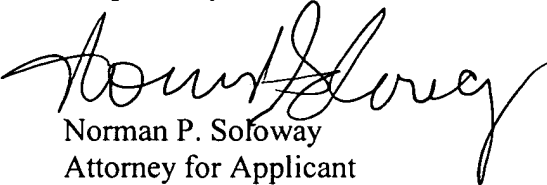
REMARKS

The claims have been amended to remove multiple dependencies. The Applicant requests that the filing fee be calculated based on the claims as amended. Examination of the application, as amended, is respectfully requested.

Pursuant to 35 CFR 1.121, a marked copy of the amended claims showing changes made therein accompanies this amendment.

In the event there are any fee deficiencies or additional fees are payable, please charge them (or credit any overpayment) to our deposit account number 08-1391.

Respectfully submitted,



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CERTIFICATE OF EXPRESS MAILING

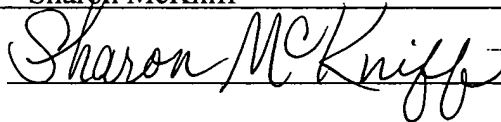
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MARKED COPY OF AMENDED CLAIMS

DOCKET: BERGLUNDS P9918

**MARKED COPY OF AMENDED CLAIMS:**

4. (Amended) A micro-hotplate device according to [any of the claims 1-3] claim 1, wherein at least one temperature-sensing element is a temperature-sensitive resistor.

5. (Amended) A micro-hotplate device according to [any of the claims 1-3] claim 1, wherein at least one temperature-sensing element is a temperature-sensitive diode.

6. (Amended) A micro-hotplate device according to [any of the claims 1-5] claim 1, wherein said membrane consists of one or several insulator layers.

8. (Amended) A micro-hotplate device according to claim 6 [or 7], wherein electrically conducting leads to the active microelectronic devices on the island have been placed between different insulator layers.

9. (Amended) A micro-hotplate device according to [any of the claims 1-8] claim 1, wherein the semiconducting material in the island is silicon.

10. (Amended) A micro-hotplate device according to [any of the claims 1-8] claim 1, wherein the semiconducting material in the island is silicon carbide.

11. (Amended) A micro-hotplate device according to [any of the claims 1-10] claim 1, wherein the support substrate and the island are made of the same material.

17. (Amended) A method according to [any of the claims 1-16] claim 12, wherein at least one of said etching steps is an anisotropic potassium hydroxide etching step.

18. (Amended) A method according to [any of the claims 12-16] claim 12, wherein at least one of said etching steps is an anisotropic tetramethyl ammonium hydroxide etching step.

19. (Amended) A method according to [any of the claims 12-16] claim 12, wherein at least one of said etching steps is a deep reactive ion etching step.

20. (Amended) A micro-hotplate device according to [any of the claims 1-12] claim 1, wherein one or several of the chemical sensors utilize the field-effect detection mechanism.

22. (Amended) A micro-hotplate device according to [any of the claims 1-12 or 21] claim 1, wherein one or several of the chemical sensors are operated as gas sensors.

23. (Amended) A micro-hotplate device according to claim[s] 21[ and 22], wherein one or several field-effect gas sensors are combined with one or several gas sensors that utilize resistance changes as detection mechanism.

26. (Amended) A micro-hotplate device according to [any of the claims 1-12 or 20-25] claim 1, wherein the support substrate contains an array of several islands.